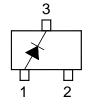
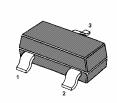
SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for low power rectification and switching power supply

Features

- Small surface mounting type.
- High reliability.





SOT-23

SOT-23 Plastic Package

Marking

Marking Code: FE

Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit	
Peak Reverse Voltage	V _{RM}	40	V	
DC Reverse Voltage	V _R	20	V	
Mean Rectifying Current	lo	0.5	А	
Peak Forward Surge Current ¹⁾	I _{FSM}	3	А	
Junction Temperature	Tj	125	°C	
Storage Temperature Range	Ts	-40 to +125	°C	

 $^{\rm 1)}$ 60Hz for 1 $\,\, \bigcirc$

Characteristics at $T_a = 25 \ ^{\circ}C$

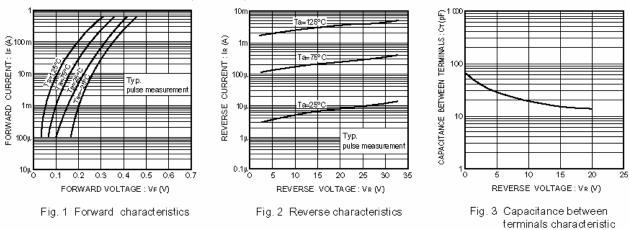
Parameter	Symbol	Min	Тур	Max	Unit
Forward Voltage					
at $I_F = 10 \text{mA}$	V_{F}	-	-	0.3	V
at $I_F = 500 \text{mA}$		-	-	0.5	
Reverse Current				20	
at V _R =10V	I _R	-	-	30	μA
Capacitance Between Terminals	C		20		~
at V _R =10V, f=1MHz	CT	-	20	-	pF







Dated : 21/10/2005



• Electrical characteristic curves (Ta = 25°C)







Dated : 21/10/2005